

	Type	L #	Hits	Search Text	DBs	Time Stamp
1	BRS	L1	17	rathi near sudha.in.	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2004/12/0 2 16:05
2	BRS	L2	69	ahn near sang.in.	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2004/12/0 2 16:06
3	BRS	L3	13	wang near yuxiang.in.	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2004/12/0 2 16:21

	Type	L #	Hits	Search Text	DBs	Time Stamp
4	BRS	L4	0	sivetti near marlo.in.	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2004/12/0 2 16:22
5	BRS	L5	0	silvetti near marlo.in.	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2004/12/0 2 16:23
6	BRS	L6	9	silvetti near mario.in.	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2004/12/0 2 16:23

	Type	L #	Hits	Search Text	DBs	Time Stamp
7	BRS	L7	2	fung near miguel.in.	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2004/12/0 2 16:24
8	BRS	L8	1	jung near keebum.in.	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2004/12/0 2 16:24
9	BRS	L9	21	zhu near lei.in.	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2004/12/0 2 16:25

	Type	L #	Hits	Search Text	DBs	Time Stamp
10	BRS	L10	0	"438"".""706".ccls.	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2004/12/0 2 16:25
11	BRS	L11	1542	438/706.ccls.	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2004/12/0 2 16:25
12	BRS	L12	42050 0	(arc or anti- reflective)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2004/12/0 2 16:26

	Type	L #	Hits	Search Text	DBs	Time Stamp
13	BRS	L13	3	(arc or anti-reflective) near15 (oxygen-free) near (silane)	US-PGPUB; USPAT; EPO; JPO; DERWE NT; IBM_T DB	2004/12/02 16:28
14	BRS	L14	6	(arc or anti-reflective) near15 (oxygen) near (silane)	US-PGPUB; USPAT; EPO; JPO; DERWE NT; IBM_T DB	2004/12/02 16:29
15	BRS	L15	1	(arc or anti-reflective) near15 (oxygen) near (silane) near15 (oxygen) near5 (carbon)	US-PGPUB; USPAT; EPO; JPO; DERWE NT; IBM_T DB	2004/12/02 16:29

	Type	L #	Hits	Search Text	DBs	Time Stamp
16	BRS	L16	15	(oxygen) near (silane) near15 (oxygen) near5 (carbon)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2004/12/0 2 16:35
17	BRS	L17	3	(nitrogen) near (silane) near15 (oxygen) near5 (carbon)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2004/12/0 2 16:32
18	BRS	L18	113	11 and (arc or ant- reflectiv\$3)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2004/12/0 2 16:36

	Type	L #	Hits	Search Text	DBs	Time Stamp
19	BRS	L19	156	11 and (arc or anti-reflectiv\$3)	US-PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2004/12/0 2 16:36
20	BRS	L21	0	11 and ((arc or anti-reflectiv\$3) near15 (oxygen) near15 (carbond))	US-PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2004/12/0 2 16:36
21	BRS	L20	13	11 and ((arc or anti-reflectiv\$3) near15 (oxygen))	US-PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2004/12/0 2 16:36

	U	1	Document ID	Title	Current OR
1			US 6696157 B1	Diamond-like glass thin films	428/408
2			US 6423630 B1	Process for forming low K dielectric material between metal lines	438/624
3			US 6349744 B1	Manifold for modular gas box system	137/884
4			US 6070550 A	Apparatus for the stabilization of halogen-doped films through the use of multiple sealing layers	118/723E
5			US 5661093 A	Method for the stabilization of halogen-doped films through the use of multiple sealing layers	438/763

	U	1	Document ID	Title	Current OR
6			US 5093152 A	Process for protecting an optical substrate by plasma deposition	427/575
7			US 4582870 A	Dioxasilepin and dioxasilocin stabilizers	524/262
8			US 4568614 A	Steel article having a disordered silicon oxide coating thereon and method of preparing the coating	428/450
9			US 4503243 A	Dioxasilepin and dioxasilocin stabilizers	556/427
10			US 3856587 A	METHOD OF FABRICATING SEMICONDUCTOR MEMORY DEVICE GATE	438/591

	U	1	Document ID	Title	Current OR
11			US 6593615 B	Semiconductor integrated circuit device, has dielectric material formed directly on planar upper surface region of layer of lower dielectric material between spaced-apart conductive structures	
12			US 20020119315 A	Formation of low dielectric constant silicon oxide dielectric material involves reacting oxidizing agent with silane(s) having oxygen or carbon atoms bonded to fluorine atom(s) and/or organofluoro moiety(ies)	
13	X		US 6348421 B	Dielectric film with low dielectric constant formation for semiconductor integrated circuit device fabrication, involves biasing chemical vapor deposition reactor of gas mixture, to deposit carbon-doped silicon oxide	

	U	1	Document ID	Title	Current OR
14	X		EP 387403 A	Low temp. chemical vapour deposition of silicon di:oxide - using mixt. of 2-6 carbon alkyl silane, oxygen and carbon di:oxide, useful in semiconductor mfr.	
15	X		RO 71157 A	Silicon vapour-plating with silicon di:oxide - from di:chloro-silane, oxygen or carbon di:oxide mixt. in radio-frequency-heated quartz reactor	